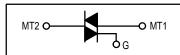
# **Triacs** Silicon Bidirectional Thyristors

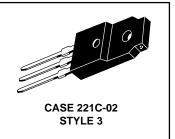
... designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity
  and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC210FP Series) or Four Modes (MAC210AFP Series)



ISOLATED TRIACs THYRISTORS 10 AMPERES RMS 200 thru 800 VOLTS

MAC210FP Series MAC210AFP Series



#### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted.)

Rating	Symbol	Value	Unit	
Repetitive Peak Off-State Voltage <sup>(1)</sup> (T <sub>J</sub> = -40 to +125°C) 1/2 Sine Wave 50 to 60 Hz, Gate Open	VDRM		Volts	
MAC210-4FP, MAC210A4FP		200		
MAC210-6FP, MAC210A6FP		400		
MAC210-8FP, MAC210A8FP MAC210-10FP, MAC210A10FP		600 800		
On-State RMS Current (T <sub>C</sub> = +70°C) Full Cycle Sine Wave 50 to 60 Hz <sup>(2)</sup>	IT(RMS)	10	Amps	
Peak Nonrepetitive Surge Current (One Full Cycle, 60 Hz, T <sub>C</sub> = +70°C) preceded and followed by rated current	ITSM	100	Amps	
Circuit Fusing (t = 8.3 ms)	l <sup>2</sup> t	40	A <sup>2</sup> s	
Peak Gate Power (T <sub>C</sub> = +70°C, Pulse Width = 10 $\mu$ s)	PGM	20	Watts	
Average Gate Power ( $T_C = +70^{\circ}C$ , t = 8.3 ms)	PG(AV)	0.35	Watt	
Peak Gate Current (T <sub>C</sub> = +70°C, Pulse Width = 10 $\mu$ s)	I <sub>GM</sub>	2	Amps	
RMS Isolation Voltage (T <sub>A</sub> = 25°C, Relative Humidity $\leq$ 20%)	V <sub>(ISO)</sub>	1500	Volts	
Operating Junction Temperature	TJ	-40 to +125	٥°	
Storage Temperature Range	T <sub>stg</sub>	-40 to +125	٥°	

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	2.2	°C/W
Thermal Resistance, Case to Sink	R <sub>0</sub> CS	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	60	°C/W

1. V<sub>DRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

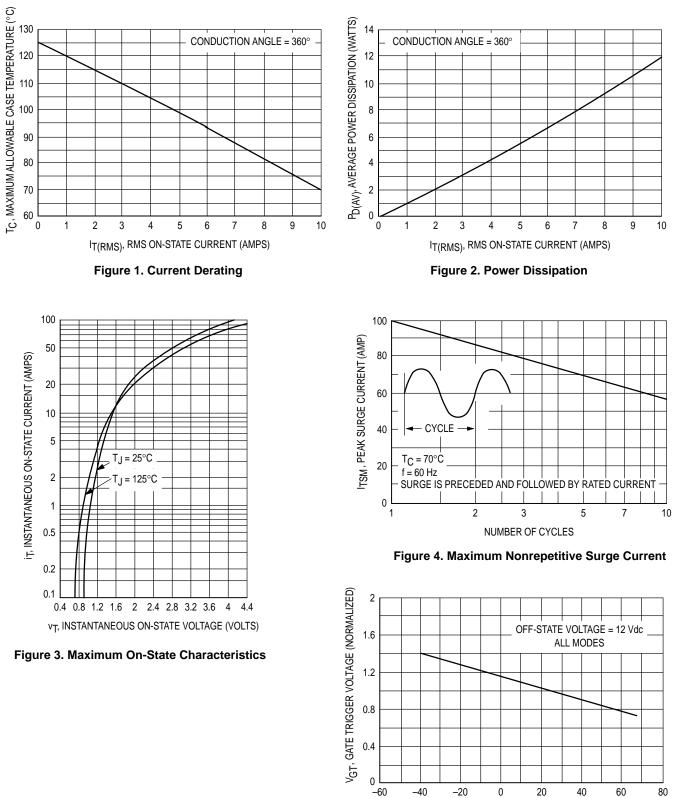
 $2. The case temperature reference point for all {\sf T}_C measurements is a point on the center lead of the package as close as possible to the plastic body.$ 



## **MAC210FP Series MAC210AFP Series**

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current (Either Direction) (V <sub>D</sub> = Rated V <sub>DRM</sub> , Gate Open) $T_J = 25^{\circ}C$ $T_J = +125^{\circ}C$	IDRM		_	10 2	μA mA
Peak On-State Voltage (Either Direction) ( $I_{TM}$ = 14 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle $\leq 2\%$ )	V <sub>TM</sub>	-	1.2	1.65	Volts
Gate Trigger Current (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100$ Ohms Minimum Gate Pulse Width = 2 µs) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY	lGT	 	12 12 20 35	50 50 50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100$ Ohms Minimum Gate Pulse Width = 2 µs) MT2(+), G(+) MT2(-), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY (Main Terminal Voltage = Rated V <sub>DRM</sub> , $R_L = 10$ k $\Omega$ , $T_J = +125^{\circ}$ C MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY	VGT	   0.2 0.2	0.9 0.9 1.1 1.4 	2 2 2.5 —	Volts
Holding Current (Either Direction) (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = 500 mA, $T_C = +25^{\circ}C$ )	Ч	-	6	50	mA
Turn-On Time (Rated V <sub>DRM</sub> , I <sub>TM</sub> = 14 A, I <sub>GT</sub> = 120 mA, Rise Time = 0.1 $\mu$ s, Pulse Width = 2 $\mu$ s)	<sup>t</sup> gt	-	1.5	—	μs
Critical Rate of Rise of Commutation Voltage (V <sub>D</sub> = Rated V <sub>DRM</sub> , I <sub>TM</sub> = 14 A, Commutating di/dt = 5.0 A/ms, Gate Unenergized, T <sub>C</sub> = +70°C)	dv/dt <sub>(c)</sub>	-	5	—	V/µs
Critical Rate of Rise of Off-State Voltage ( $V_D$ = Rated $V_{DRM}$ , Exponential Voltage Rise, Gate Open, $T_C$ = +70°C)	dv/dt	_	100	_	V/µs

#### **MAC210FP Series MAC210AFP Series**



#### TYPICAL CHARACTERISTICS

Figure 5. Typical Gate Trigger Voltage

T<sub>C</sub>, CASE TEMPERATURE (°C)

### **MAC210FP Series MAC210AFP Series**

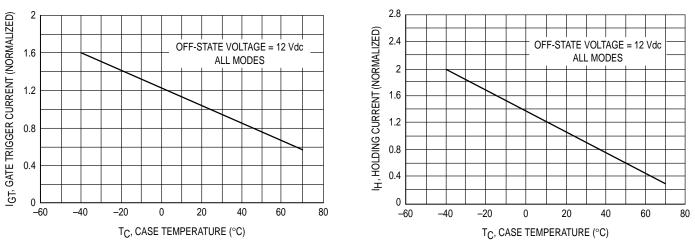


Figure 6. Typical Gate Trigger Current

Figure 7. Typical Holding Current

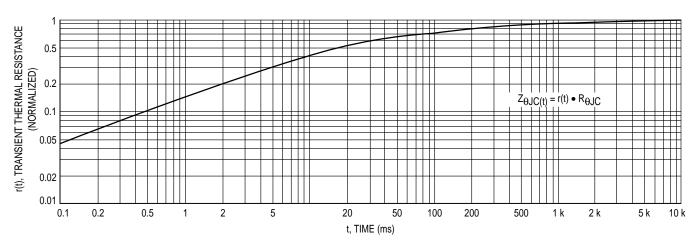
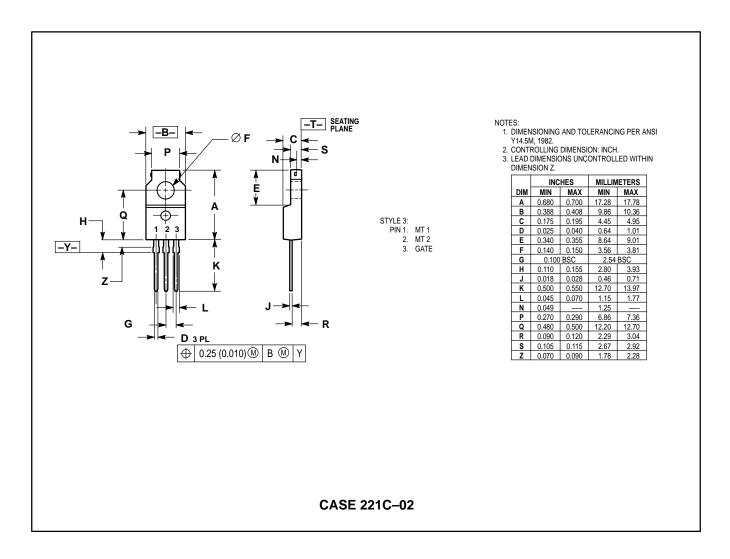


Figure 8. Thermal Response

#### PACKAGE DIMENSIONS



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